

**FEATURES**

- Red Enhanced
- Low Noise
- High Response
- High Shunt Resistance
- Low Profile TO-5 Package

**Electro-Optical Characteristics at 25°C**

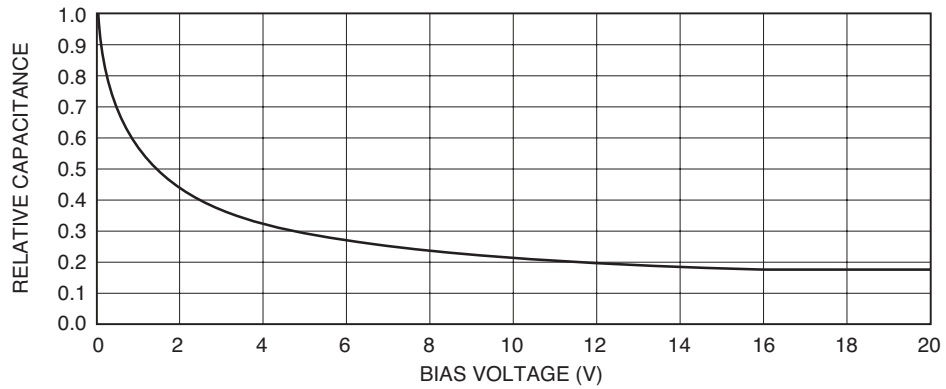
Characteristic	Test Conditions	Min	Typ	Max	Units
Dark Current, I <sub>D</sub>	V <sub>R</sub> = 5 V		0.9	5	na
Shunt Resistance, R <sub>SH</sub>	V <sub>R</sub> = 10 mV		300		MΩ
Junction Capacitance, C <sub>J</sub>	V <sub>R</sub> = 0 V, f = 1 MHz		30		pF
Junction Capacitance, C <sub>J</sub>	V <sub>R</sub> = 10 V, f = 1 MHz		7.5		pF
Spectral Application Range, λ <sub>range</sub>	Spot Scan	250		1100	nm
Responsivity, R	λ = 633 nm, V <sub>R</sub> = 0 V	0.32	0.36		A/W
Responsivity, R	λ = 900 nm, V <sub>R</sub> = 0 V	0.5	0.6		A/W
Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 10 μA	25	60		V
Noise Equivalent Power, NEP	V <sub>R</sub> = 0 V, λ = 950 nm		2.5 x 10 <sup>-14</sup>		W/√HZ
Response Time, t <sub>r</sub> <sup>1</sup>	RL = 50 Ω, V <sub>R</sub> = 0 V		190		nsec
Response Time, t <sub>r</sub> <sup>1</sup>	RL = 50 Ω, V <sub>R</sub> = 10 V		8		nsec

<sup>1</sup> Response time of 10% to 90% is specified at 660 nm.

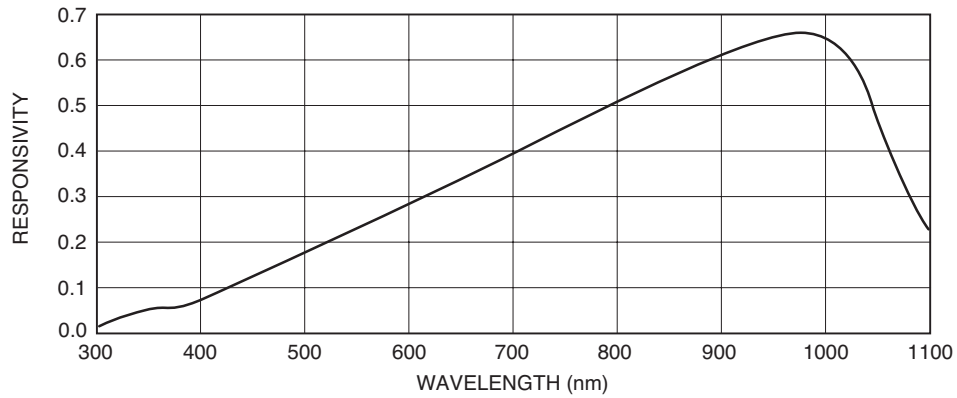
**Absolute Maximum Ratings at 25°C**

Parameter	Min	Max	Units
Reverse Voltage, V <sub>R</sub>		100	V
Storage Temperature, T <sub>STG</sub>	-55	+150	°C
Operating Temperature, T <sub>O</sub>	-40	+125	°C
Lead Soldering Temperature (1/16" from case for 3 sec)		+260	°C

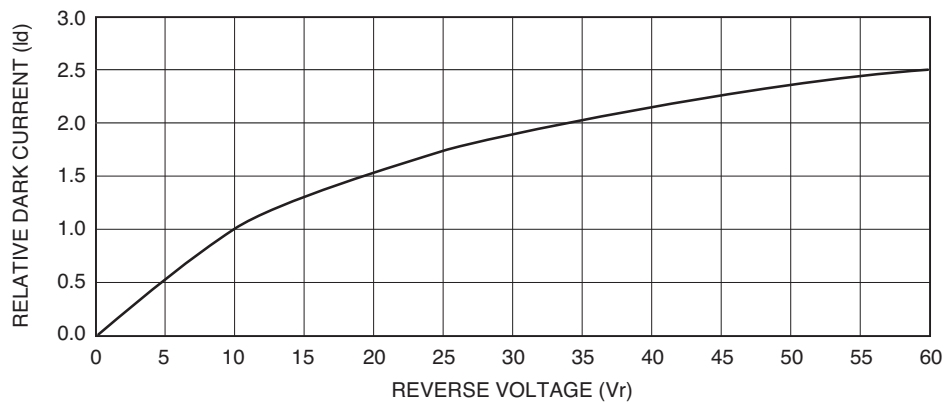
**Capacitance vs Bias Voltage**



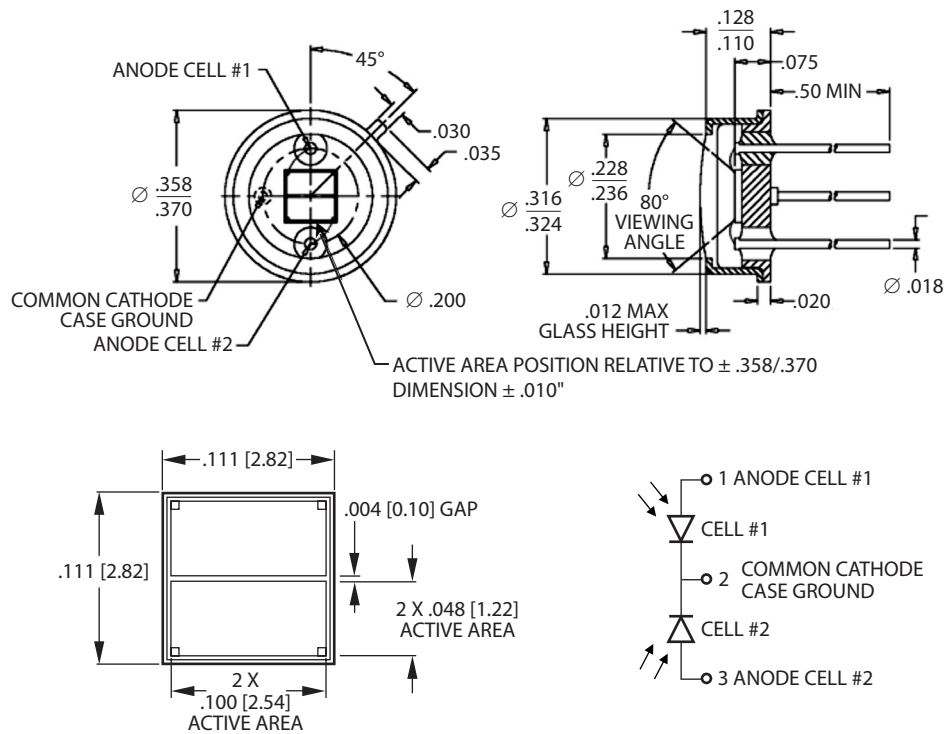
**Typical Spectral Response**



**Dark Current vs Voltage**



**Package Information**



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.